Hybrid Nextation HTC+ Series
Native Oxide Free for 5 days

Key Features

- Optimum SiHx surface termination
- Over 120 hours (5 days) of queue (staging) time
- Contamination free HF processing
- No Silicon consumption during wafer treatment
- Replaces traditional RCA cleans, rapid & efficient wafer cleaning (95% PRE)

Specifications

*Hybrid Nextation HTC+ Standard Spececation

Item		Specification	
		300mm	200mm
H/W	Configuration	FRD+Functional Water+M/S	
	Dimension	3,180(W)*2,040(D)*2,730(H)	2,350(W)*1,853(D)*2,600(H)
	Dry Main Effect	Le Chatelier's Principle	
	- Wafer Move	0.1~99mm/sec	0.1~99mm/sec
	- IPA Consumption	90cc/Batch (50Wafers)	30cc/Batch (50Wafers)
	- Bath Volume	51 Liters	40 Liters
	- Rinse Dry with DHF(FRD)	Yes	
	- Mixing method	In-situ	
	- Dryer	NEO-Series(RT IPA, 3 Bubbling)	NEO-Series(RT IPA, 2 Bubbling)
Characteristic	Comment	1 Process Bath	
		Small Foot print	
		High A/S support	
		Water Mark Free	
		Native Oxide Free for 5 Days	

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Advanced Processing Equipment Technology
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